

/ Descriptions

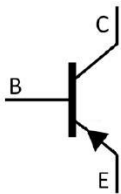
Silicon PNP transistor in a TO-92 Plastic Package.

/ Features

Low noise, high gain.

/ Applications

This device is designed for general purpose amplifier applications at collector currents from 50mA.

/ Equivalent Circuit**/ Pinning**

PIN1 Collector PIN 2 Base PIN 3 Emitter

/ h_{FE} Classifications & Marking

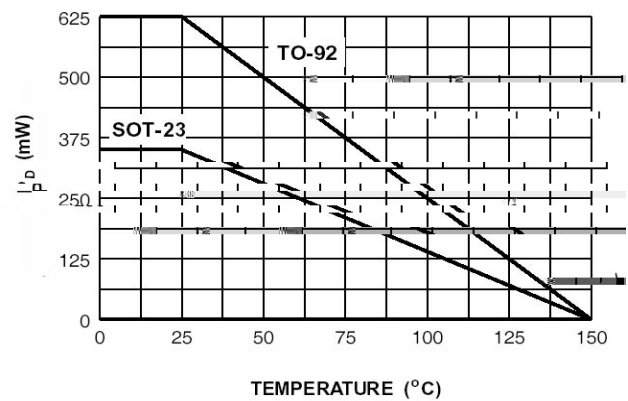
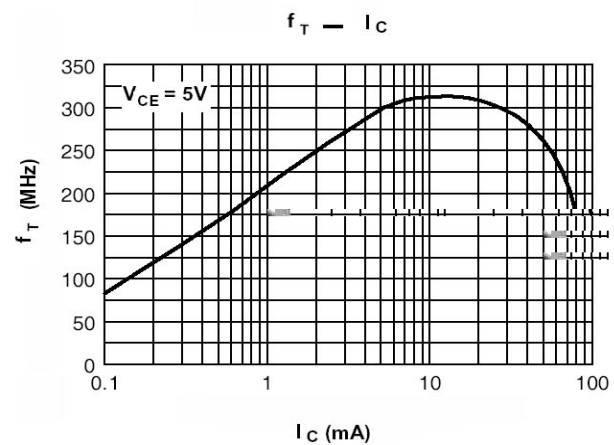
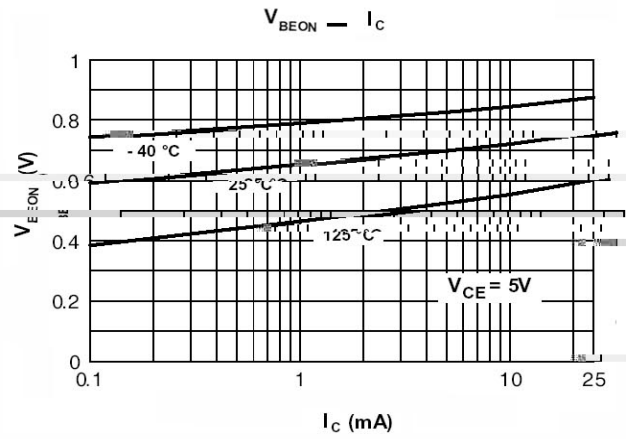
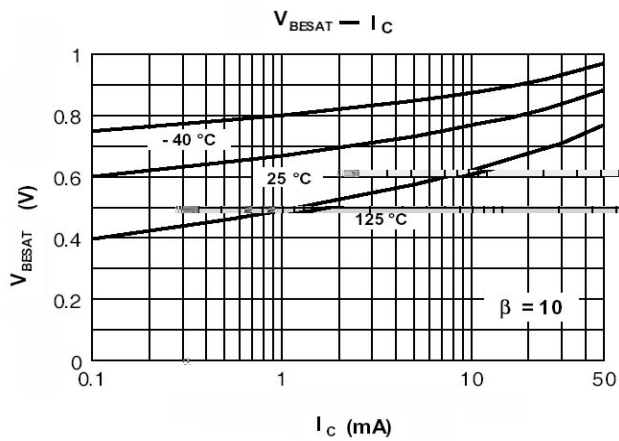
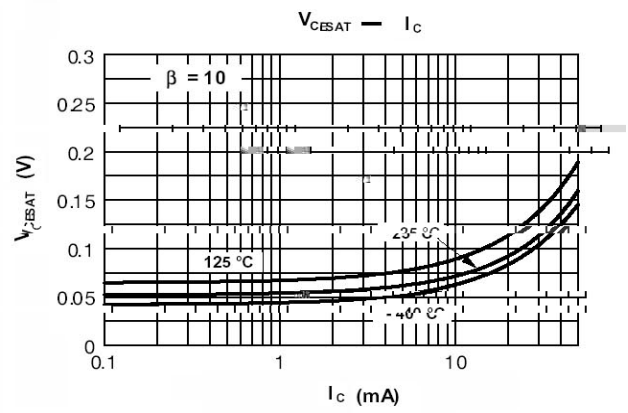
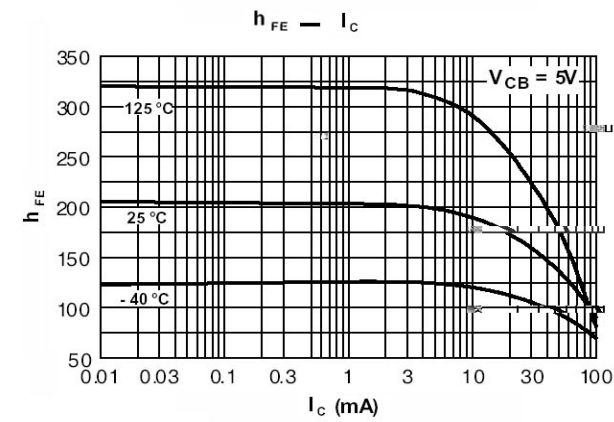
See Marking Instructions.

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-50	V
Collector to Emitter Voltage	V_{CEO}	-50	V
Emitter to Base Voltage	V_{EBO}	-3	V
Collector Current - Continuous	I_C	-50	mA
Collector Power Dissipation	P_C	625	mW
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Base Breakdown Voltage	V_{CBO}	$I_C = -100\text{ A}$ $I_E = 0$	-50			V
Collector to Emitter Breakdown Voltage	V_{CEO}	$V_{EB} = -1\text{V}$ $I_B = 0$	-50			V
Emitter Cut-Off Current	I_{EBO}	$V_{CB} = -3\text{V}$ $I_C = 0$			-50	nA

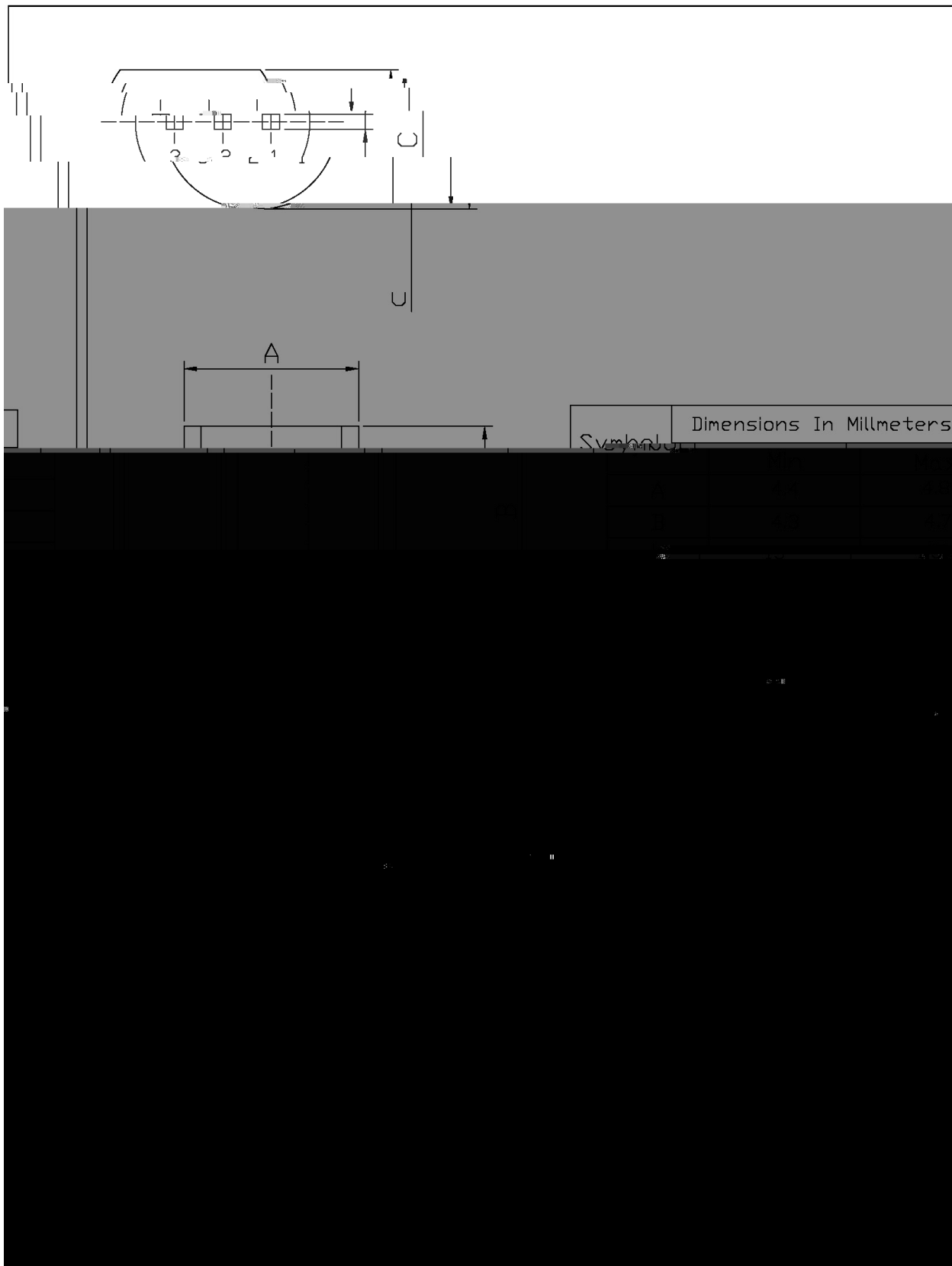


Electrical Characteristic Curve

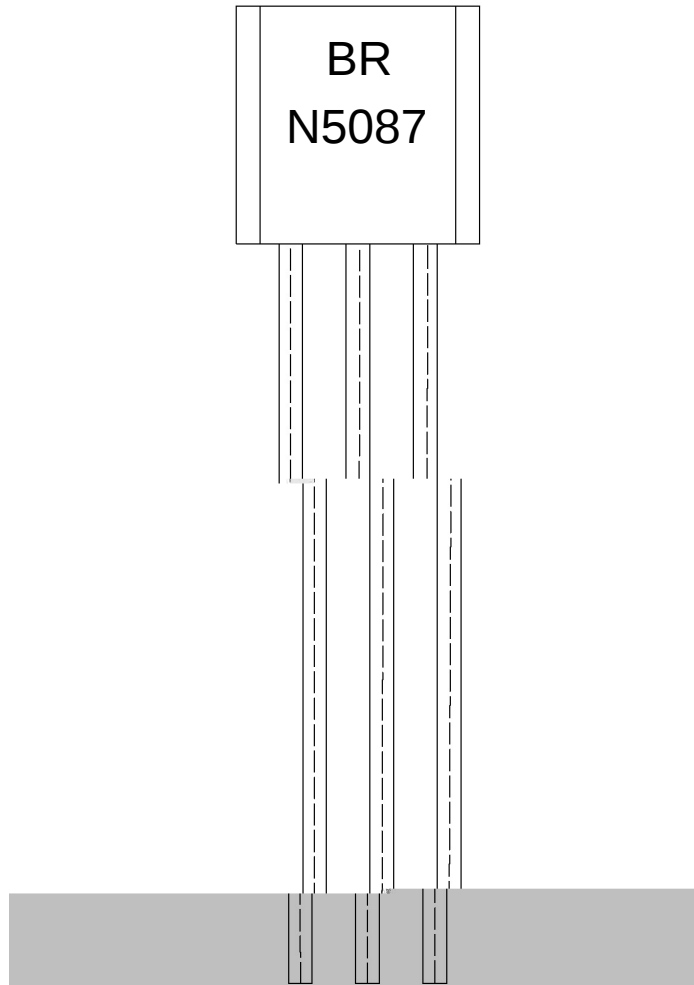


T O - 92

Unit: mm mm



/ Marking Instructions



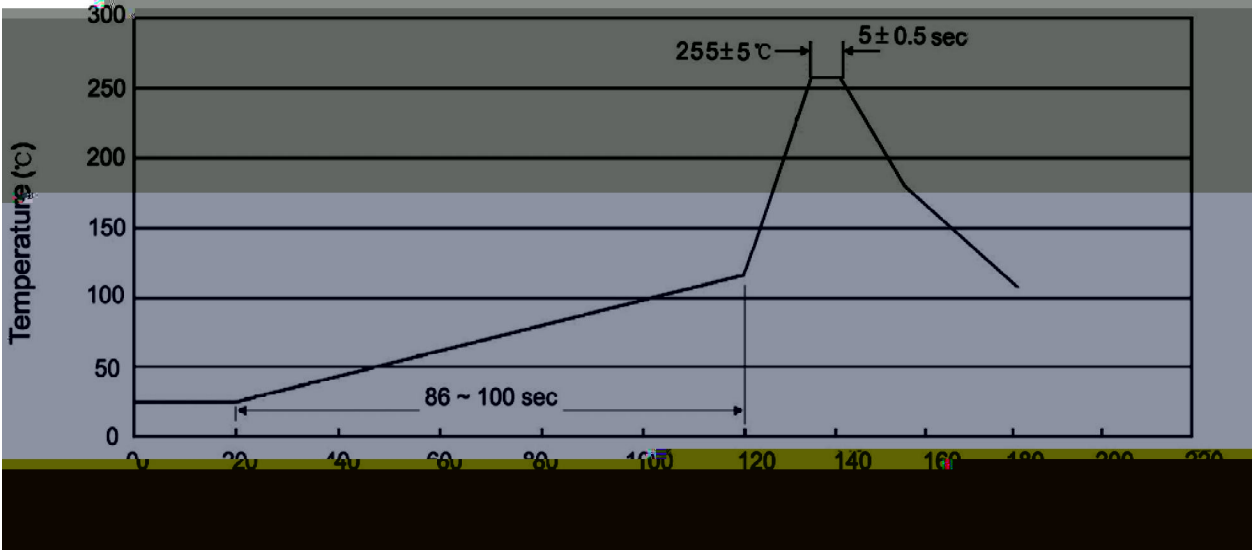
Note:

BR: Company Code.

N5087: Product Type.

***: Lot No. Code, code change with Lot No.

() / Temperature Profile for Dip Soldering(Pb-Free)



Note:

- | | | | | | |
|---|-----|-----|----|----------|---|
| 1 | 25 | 150 | 60 | 90sec; | 1.Preheating:25~150 , Time:60~90sec. |
| 2 | 255 | 5 | 5 | 0.5sec; | 2.Peak Temp.:255 5 , Duration:5 0.5sec. |
| 3 | | | 2 | 10 /sec. | 3. Cooling Speed: 2~10 /sec. |

/ Resistance to Soldering Heat Test Conditions

270 5